



100V PNP HIGH VOLTAGE TRANSISTOR IN TO252 (DPAK)

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

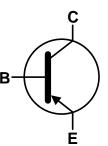
- BV_{CEO} > -100V
- I_C = -3A High Continuous Collector Current
- I_{CM} = -5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary NPN Type: MJD31CUQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

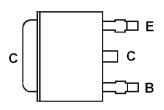
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)







Device Schematic



Pin Out Configuration Top View

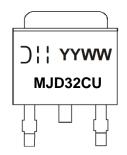
Ordering Information (Notes 4 & 5)

Part number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD32CUQ-13	Automotive	MJD32CU	13	16	2,500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-3	А
Peak Pulse Collector Current	I _{CM}	-5	А
Continuous Base Current	lΒ	-1	A
Power Dissipation	P_{D}	15	W

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		3.9	
Power Dissipation	(Note 7)	P_{D}	2.1	W
	(Note 8)		1.6	1
	(Note 6)		32	
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	59	900
	(Note 8)		80	°C/W
Thermal Resistance, Junction to Leads	(Note 9)	$R_{\theta JL}$	3.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

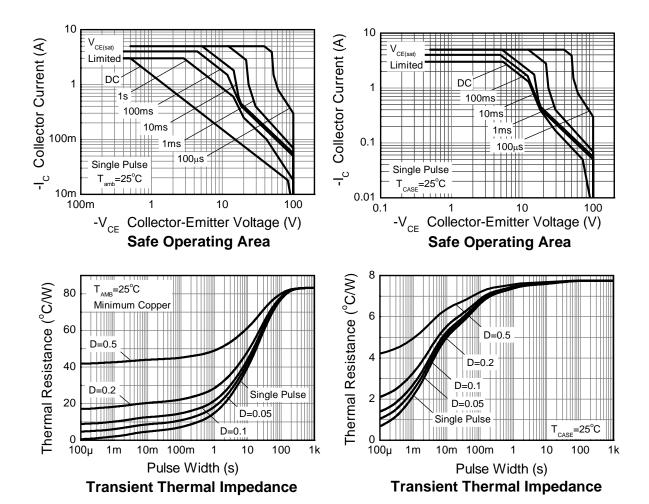
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- 9. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





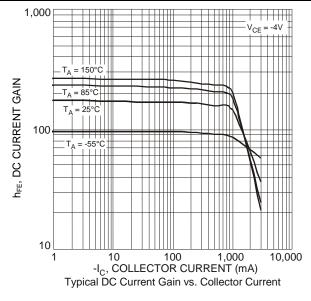
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

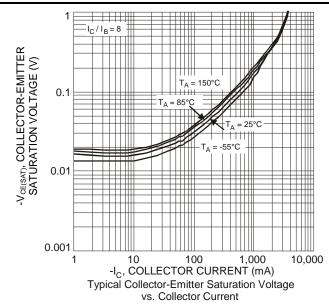
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-120	ı	I	V	I _C = -20μA
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	-100	1	I	V	$I_C = -30 \text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	1	1	V	I _E = -100μA
Collector-Base Cut-off Current	I _{CBO}	-	1	-1	μΑ	V _{CB} = -100V
Collector Cut-off Current	I _{CEO}	-	1	-1	μΑ	$V_{CE} = -60V$
Collector Cut-off Current	I _{CES}	-	1	-1	μΑ	V _{CE} = -100V
Emitter Cut-off Current	I _{EBO}	-	-	-1	μΑ	V _{EB} = -5V
	V _{CE(sat)}	-	1	-300	mV	I _C = -1A, I _B = -100mA
Collector-Emitter Saturation Voltage (Note 11)		-	1	-500	mV	$I_C = -2A$, $I_B = -200mA$
(Note 11)	, ,	-	1	-700	mV	$I_C = -3A$, $I_B = -375mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	-	-	-1.2	V	I _C = -2A, I _B = -200mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	=	-	-950	mV	$I_C = -1A$, $V_{CE} = -2V$
base-Emilier rum-On voltage (Note 11)		ı	ı	-1.4	V	$I_{C} = -3A$, $V_{CE} = -4V$
DC Current Gain (Note 11)	h _{FE}	25		1		$V_{CE} = -4V$, $I_C = -1A$
DC Current Gain (Note 11)		10		50	_	$V_{CE} = -4V$, $I_C = -3A$
Current Signal Current Gain	H _{fe}	20			_	$V_{CE} = -10V$, $I_{C} = -0.5A$, $f = 1kHz$
Current Gain-Bandwidth Product	f_T	3.0	-	-	MHz	$I_C = -0.5A$, $V_{CE} = -10V$, $f = 1MHz$

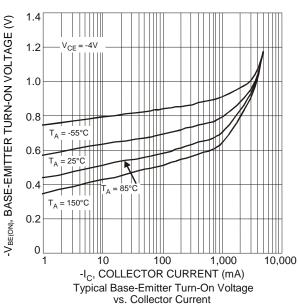
Note: 11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

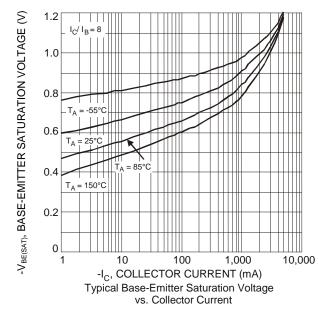


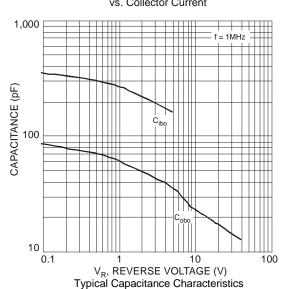
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)









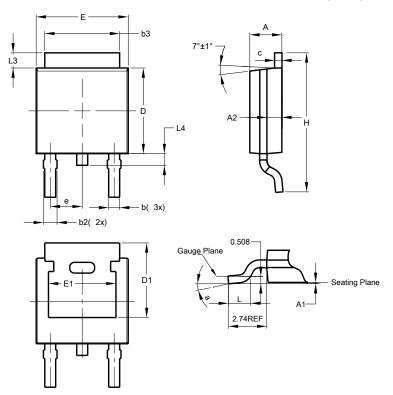




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

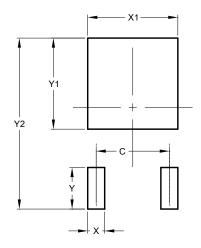


TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
A1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
b	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-	-	
е	-	-	2.286	
Е	6.45	6.70	6.58	
E1	4.32	-	-	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	-	
All Dimensions in mm				

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Χ	1.060			
X1	5.632			
Υ	2.600			
Y1	5.700			
Y2	10.700			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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